

SOT-523 Plastic-Encapsulate Diodes

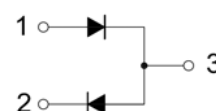
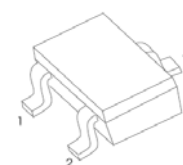
SCHOTTKY BARRIER DIODE

FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

MARKING:A7

SOT-523



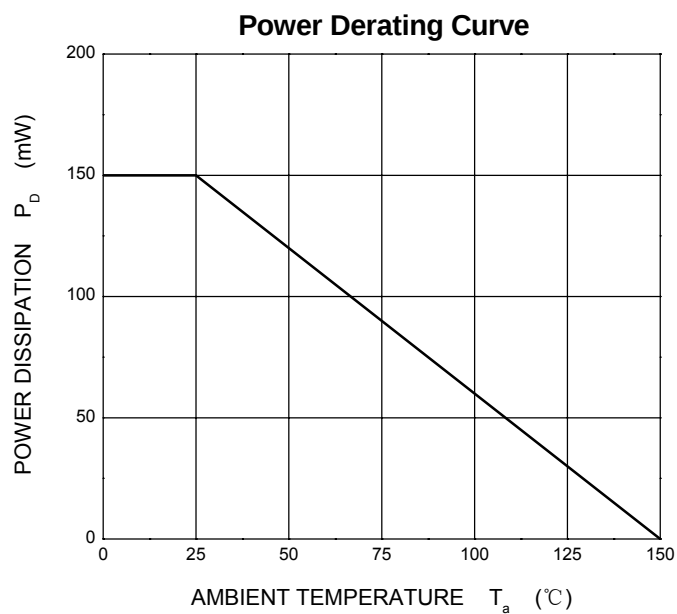
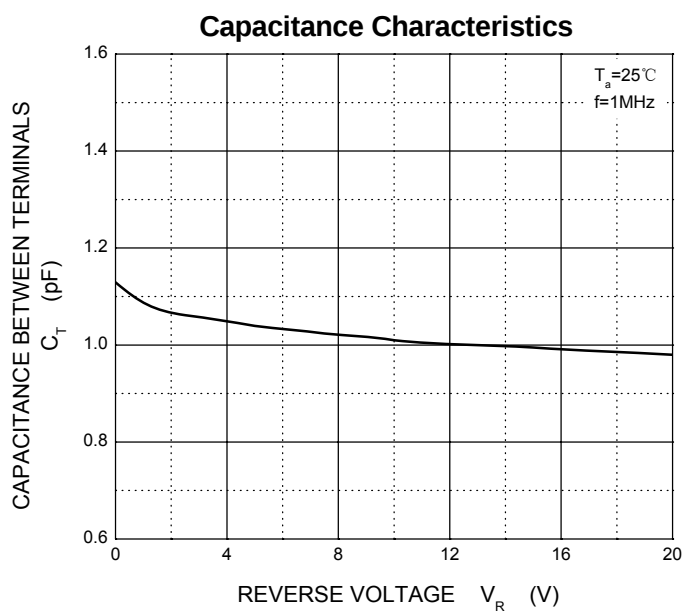
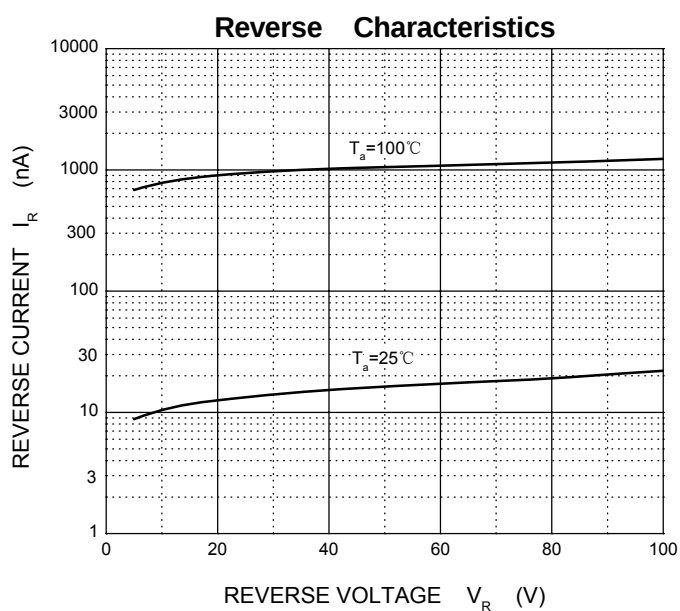
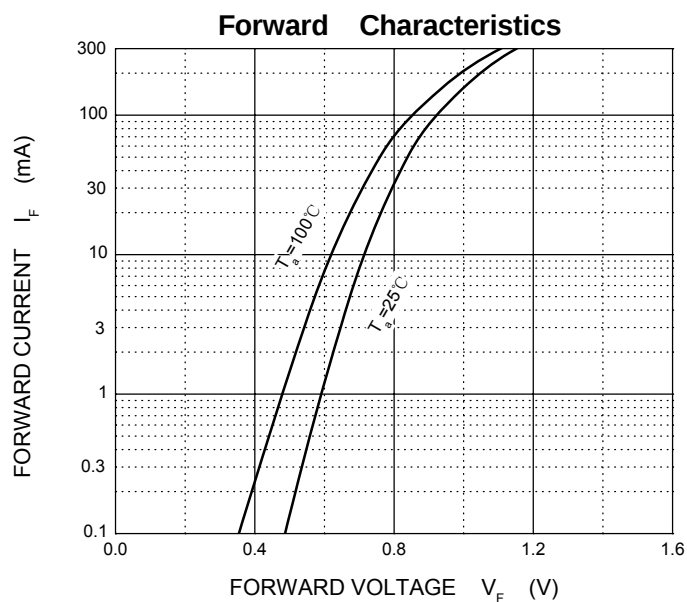
Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Reverse Voltage	V_R	85	V
Forward Current	I_F	75	mA
Non-Repetitive Peak Forward Surge Current @ t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

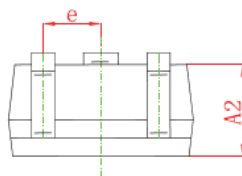
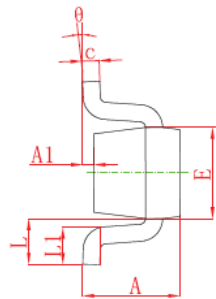
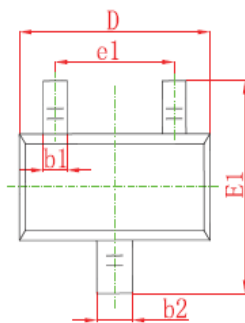
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1\mu A$	85		V
Reverse voltage leakage current	I_{R1}	$V_R = 75V$		2	μA
	I_{R2}	$V_R = 25V$		0.03	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0$ $f = 1MHz$		1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$		4	ns

Typical Characteristics

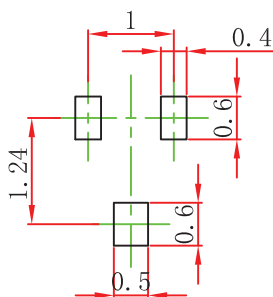


SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°

SOT-523 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

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